



# BUK9K17-60E

Dual N-channel 60 V, 17 mΩ logic level MOSFET

19 March 2014

Product data sheet

## 1. General description

Dual logic level N-channel MOSFET in an LPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

## 2. Features and benefits

- Dual MOSFET
- Q101 Compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with  $V_{GS(th)}$  rating of greater than 0.5 V at 175 °C

## 3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

## 4. Quick reference data

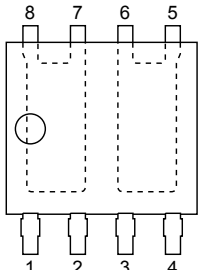
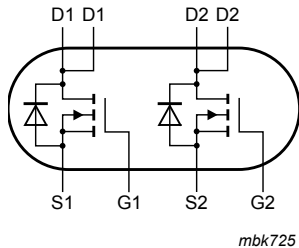
Table 1. Quick reference data

| Symbol                                       | Parameter                        | Conditions                                                                                                                                      |     | Min | Typ | Max | Unit |
|----------------------------------------------|----------------------------------|-------------------------------------------------------------------------------------------------------------------------------------------------|-----|-----|-----|-----|------|
| $V_{DS}$                                     | drain-source voltage             | $T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$                                                                                              |     | -   | -   | 60  | V    |
| $I_D$                                        | drain current                    | $V_{GS} = 5\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>                                                                        | [1] | -   | -   | 26  | A    |
| $P_{tot}$                                    | total power dissipation          | $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>                                                                                                |     | -   | -   | 53  | W    |
| <b>Static characteristics FET1 and FET2</b>  |                                  |                                                                                                                                                 |     |     |     |     |      |
| $R_{DS(on)}$                                 | drain-source on-state resistance | $V_{GS} = 5\text{ V}$ ; $I_D = 10\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 11</a>                                                    |     | -   | 14  | 17  | mΩ   |
| <b>Dynamic characteristics FET1 and FET2</b> |                                  |                                                                                                                                                 |     |     |     |     |      |
| $Q_{GD}$                                     | gate-drain charge                | $I_D = 10\text{ A}$ ; $V_{DS} = 48\text{ V}$ ; $V_{GS} = 5\text{ V}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a> |     | -   | 5.7 | -   | nC   |

[1] Continuous current is limited by package.

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline                                                                                      | Graphic symbol                                                                                |
|-----|--------|-------------|---------------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------------|
| 1   | S1     | source1     | <br>LFPAK56D (SOT1205) | <br>mbk725 |
| 2   | G1     | gate1       |                                                                                                         |                                                                                               |
| 3   | S2     | source2     |                                                                                                         |                                                                                               |
| 4   | G2     | gate2       |                                                                                                         |                                                                                               |
| 5   | D2     | drain2      |                                                                                                         |                                                                                               |
| 6   | D2     | drain2      |                                                                                                         |                                                                                               |
| 7   | D1     | drain1      |                                                                                                         |                                                                                               |
| 8   | D1     | drain1      |                                                                                                         |                                                                                               |

## 6. Ordering information

Table 3. Ordering information

| Type number | Package  |                                                                  |         |
|-------------|----------|------------------------------------------------------------------|---------|
|             | Name     | Description                                                      | Version |
| BUK9K17-60E | LFPAK56D | Plastic single ended surface mounted package (LFPAK56D); 8 leads | SOT1205 |

## 7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| BUK9K17-60E | 91760E       |

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol    | Parameter               | Conditions                                                |        | Min | Max | Unit |
|-----------|-------------------------|-----------------------------------------------------------|--------|-----|-----|------|
| $V_{DS}$  | drain-source voltage    | $T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$        |        | -   | 60  | V    |
| $V_{DGR}$ | drain-gate voltage      | $R_{GS} = 20\text{ k}\Omega$                              |        | -   | 60  | V    |
| $V_{GS}$  | gate-source voltage     | $T_j \leq 175\text{ °C}$ ; DC                             |        | -10 | 10  | V    |
|           |                         | $T_j \leq 175\text{ °C}$ ; Pulsed                         | [1][2] | -15 | 15  | V    |
| $P_{tot}$ | total power dissipation | $T_{mb} = 25\text{ °C}$ ; Fig. 1                          |        | -   | 53  | W    |
| $I_D$     | drain current           | $T_{mb} = 25\text{ °C}$ ; $V_{GS} = 5\text{ V}$ ; Fig. 2  | [3]    | -   | 26  | A    |
|           |                         | $T_{mb} = 100\text{ °C}$ ; $V_{GS} = 5\text{ V}$ ; Fig. 2 |        | -   | 26  | A    |

| Symbol                             | Parameter                                    | Conditions                                                                                                                   |                        | Min | Max | Unit |
|------------------------------------|----------------------------------------------|------------------------------------------------------------------------------------------------------------------------------|------------------------|-----|-----|------|
| I <sub>DM</sub>                    | peak drain current                           | T <sub>mb</sub> = 25 °C; pulsed; t <sub>p</sub> ≤ 10 μs; <a href="#">Fig. 3</a>                                              |                        | -   | 148 | A    |
| T <sub>stg</sub>                   | storage temperature                          |                                                                                                                              |                        | -55 | 175 | °C   |
| T <sub>j</sub>                     | junction temperature                         |                                                                                                                              |                        | -55 | 175 | °C   |
| Source-drain diode FET1 and FET2   |                                              |                                                                                                                              |                        |     |     |      |
| I <sub>S</sub>                     | source current                               | T <sub>mb</sub> = 25 °C                                                                                                      | <a href="#">[3]</a>    | -   | 26  | A    |
| I <sub>SM</sub>                    | peak source current                          | pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C                                                                      |                        | -   | 148 | A    |
| Avalanche Ruggedness FET1 and FET2 |                                              |                                                                                                                              |                        |     |     |      |
| E <sub>DS(AL)S</sub>               | non-repetitive drain-source avalanche energy | I <sub>D</sub> = 26 A; V <sub>sup</sub> ≤ 60 V; V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; <a href="#">Fig. 4</a> | <a href="#">[4][5]</a> | -   | 64  | mJ   |

- [1] Accumulated Pulse duration up to 50 hours delivers zero defect ppm
- [2] Significantly longer life times are achieved by lowering T<sub>j</sub> and or V<sub>GS</sub>.
- [3] Continuous current is limited by package.
- [4] Refer to application note AN10273 for further information
- [5] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C

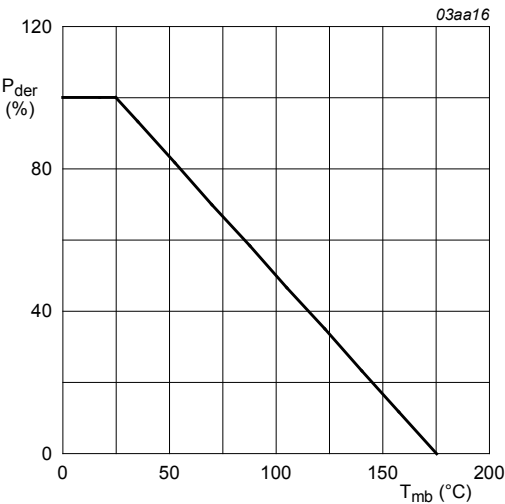


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

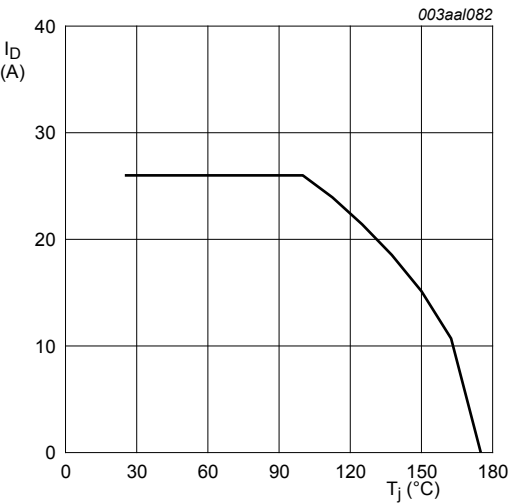


Fig. 2. Continuous drain current as a function of mounting base temperature

$$V_{GS} \geq 5V$$

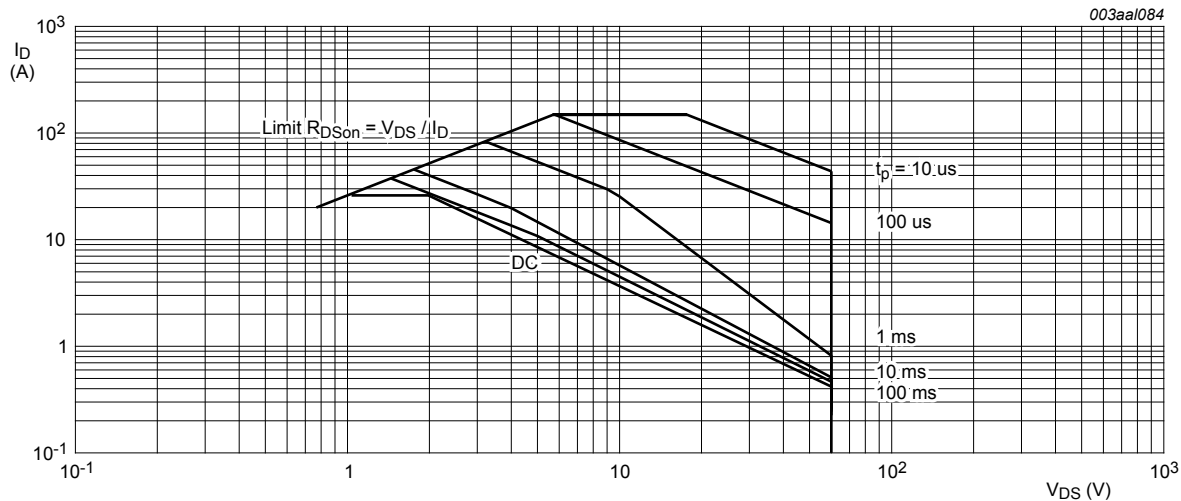


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25^{\circ}C$ ;  $I_{DM}$  is a single pulse

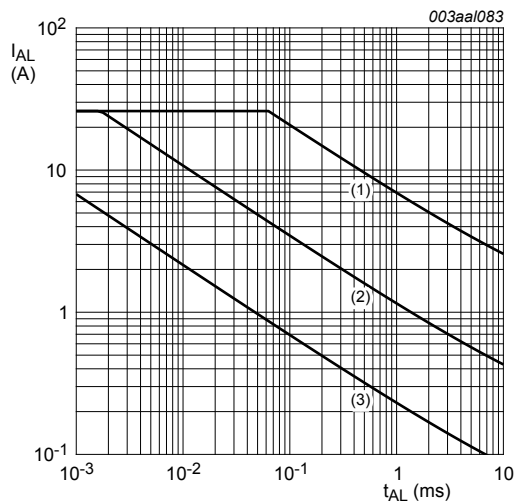


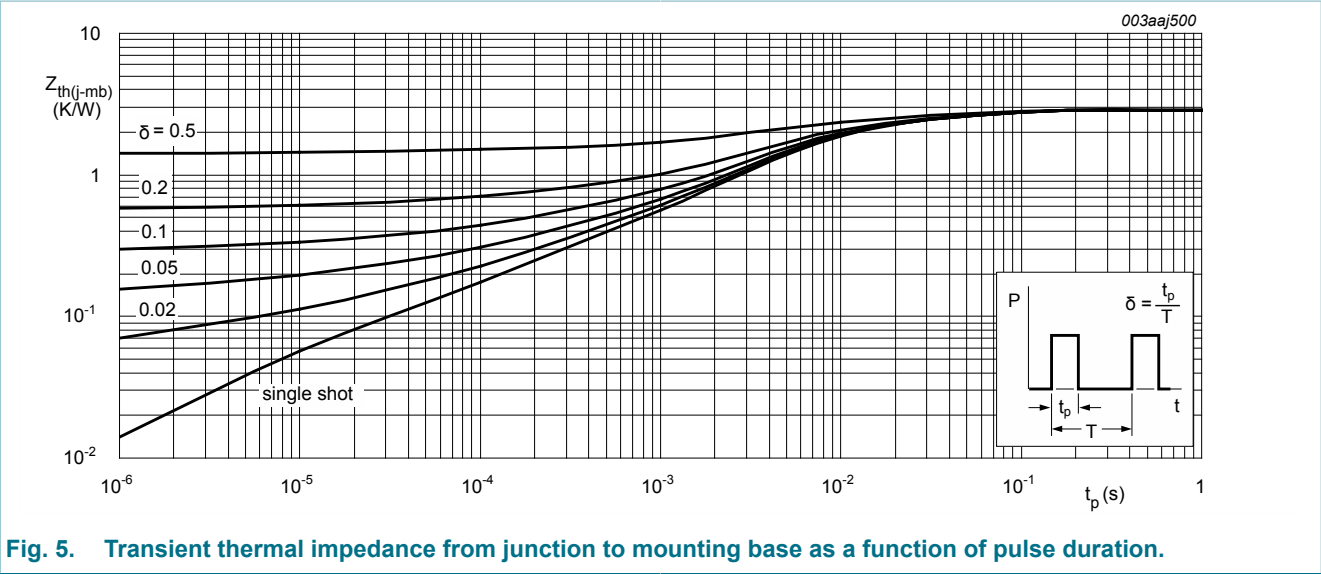
Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

(1)  $T_{j (init)} = 25^{\circ}C$ ; (2)  $T_{j (init)} = 150^{\circ}C$ ; (3) Repetitive Avalanche

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter                                         | Conditions                                            | Min | Typ | Max  | Unit |
|----------------|---------------------------------------------------|-------------------------------------------------------|-----|-----|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | Fig. 5                                                | -   | -   | 2.84 | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient       | Minimum footprint; mounted on a printed circuit board | -   | 95  | -    | K/W  |



10. Characteristics

Table 7. Characteristics

| Symbol                                | Parameter                        | Conditions                                                                                                                                      |  | Min | Typ  | Max  | Unit |
|---------------------------------------|----------------------------------|-------------------------------------------------------------------------------------------------------------------------------------------------|--|-----|------|------|------|
| Static characteristics FET1 and FET2  |                                  |                                                                                                                                                 |  |     |      |      |      |
| V <sub>(BR)DSS</sub>                  | drain-source breakdown voltage   | I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>J</sub> = -55 °C                                                                         |  | 54  | -    | -    | V    |
|                                       |                                  | I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 25 °C                                                                          |  | 60  | -    | -    | V    |
| V <sub>GS(th)</sub>                   | gate-source threshold voltage    | I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>J</sub> = 25 °C; <a href="#">Fig. 9</a> ; <a href="#">Fig. 10</a>             |  | 1.4 | 1.7  | 2.1  | V    |
|                                       |                                  | I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>J</sub> = 175 °C; <a href="#">Fig. 9</a> ; <a href="#">Fig. 10</a>            |  | 0.5 | -    | -    | V    |
|                                       |                                  | I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>J</sub> = -55 °C; <a href="#">Fig. 9</a> ; <a href="#">Fig. 10</a>            |  | -   | -    | 2.45 | V    |
| I <sub>DSS</sub>                      | drain leakage current            | V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 25 °C                                                                           |  | -   | 0.02 | 1    | μA   |
|                                       |                                  | V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 175 °C                                                                          |  | -   | -    | 500  | μA   |
| I <sub>GSS</sub>                      | gate leakage current             | V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>J</sub> = 25 °C                                                                          |  | -   | 2    | 100  | nA   |
|                                       |                                  | V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>J</sub> = 25 °C                                                                           |  | -   | 2    | 100  | nA   |
| R <sub>DSon</sub>                     | drain-source on-state resistance | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 10 A; T <sub>J</sub> = 25 °C; <a href="#">Fig. 11</a>                                                   |  | -   | 14   | 17   | mΩ   |
|                                       |                                  | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 10 A; T <sub>J</sub> = 175 °C; <a href="#">Fig. 11</a> ; <a href="#">Fig. 12</a>                        |  | -   | 31.6 | 38.4 | mΩ   |
|                                       |                                  | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 10 A; T <sub>J</sub> = 25 °C; <a href="#">Fig. 11</a>                                                  |  | -   | 12.4 | 15.6 | mΩ   |
| Dynamic characteristics FET1 and FET2 |                                  |                                                                                                                                                 |  |     |      |      |      |
| Q <sub>G(tot)</sub>                   | total gate charge                | I <sub>D</sub> = 10 A; V <sub>DS</sub> = 48 V; V <sub>GS</sub> = 5 V; T <sub>J</sub> = 25 °C; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a> |  | -   | 16.5 | -    | nC   |
| Q <sub>GS</sub>                       | gate-source charge               |                                                                                                                                                 |  | -   | 3.3  | -    | nC   |

| Symbol                           | Parameter                    | Conditions                                                                                 |  | Min | Typ  | Max  | Unit |
|----------------------------------|------------------------------|--------------------------------------------------------------------------------------------|--|-----|------|------|------|
| $Q_{GD}$                         | gate-drain charge            |                                                                                            |  | -   | 5.7  | -    | nC   |
| $C_{iss}$                        | input capacitance            | $V_{GS} = 0\text{ V}$ ; $V_{DS} = 25\text{ V}$ ; $f = 1\text{ MHz}$ ;                      |  | -   | 1667 | 2223 | pF   |
| $C_{oss}$                        | output capacitance           | $T_J = 25\text{ }^{\circ}\text{C}$ ; Fig. 15                                               |  | -   | 160  | 193  | pF   |
| $C_{rss}$                        | reverse transfer capacitance | $V_{GS} = 0\text{ V}$ ; $V_{DS} = 48\text{ V}$ ; $f = 1\text{ MHz}$ ;                      |  | -   | 91   | 124  | pF   |
| $t_{d(on)}$                      | turn-on delay time           | $V_{DS} = 48\text{ V}$ ; $R_L = 5\text{ }\Omega$ ; $V_{GS} = 5\text{ V}$ ;                 |  | -   | 10.7 | -    | ns   |
| $t_r$                            | rise time                    | $R_{G(ext)} = 5\text{ }\Omega$ ; $T_J = 25\text{ }^{\circ}\text{C}$ ; $I_D = 10\text{ A}$  |  | -   | 20   | -    | ns   |
| $t_{d(off)}$                     | turn-off delay time          |                                                                                            |  | -   | 23   | -    | ns   |
| $t_f$                            | fall time                    |                                                                                            |  | -   | 19.2 | -    | ns   |
| Source-drain diode FET1 and FET2 |                              |                                                                                            |  |     |      |      |      |
| $V_{SD}$                         | source-drain voltage         | $I_S = 10\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; $T_J = 25\text{ }^{\circ}\text{C}$ ; Fig. 16 |  | -   | 0.78 | 1.2  | V    |
| $t_{rr}$                         | reverse recovery time        | $I_S = 10\text{ A}$ ; $di_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ;      |  | -   | 20.3 | -    | ns   |
| $Q_r$                            | recovered charge             | $V_{DS} = 30\text{ V}$ ; $T_J = 25\text{ }^{\circ}\text{C}$                                |  | -   | 16.7 | -    | nC   |

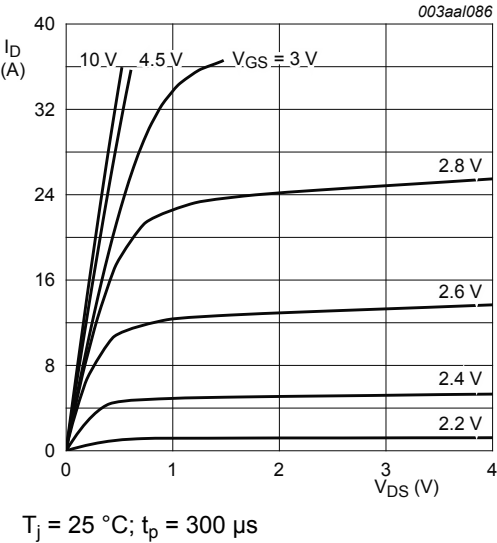


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

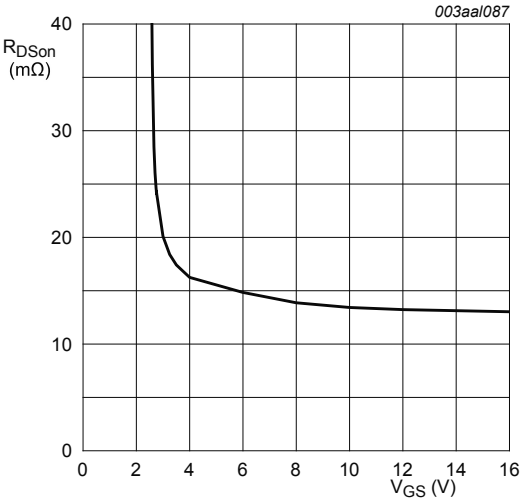


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_J = 25\text{ }^{\circ}\text{C}$ ;  $I_D = 10\text{ A}$

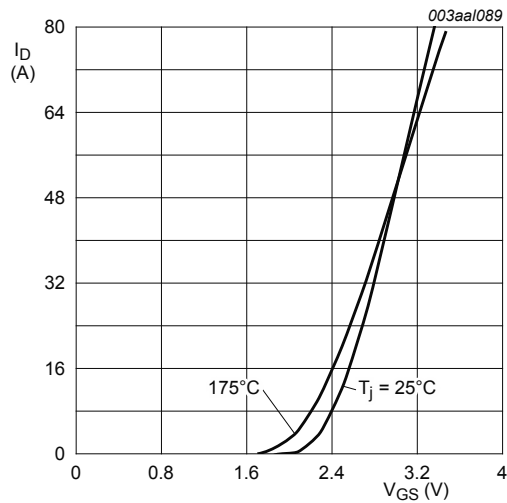


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$V_{DS} = 10\text{ V}$

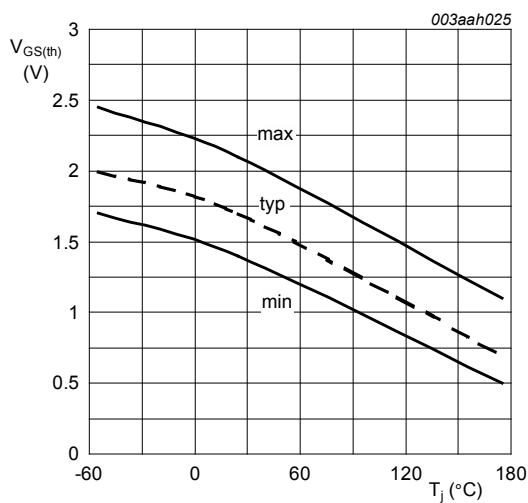


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

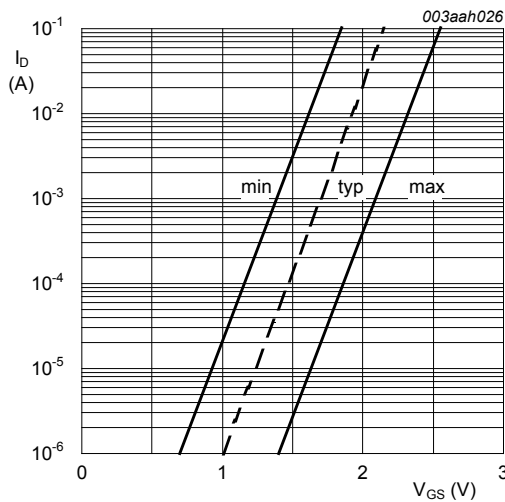


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25^\circ\text{C}; V_{DS} = 5\text{ V}$

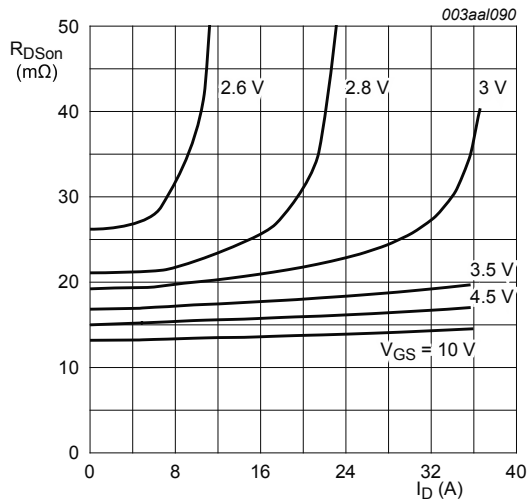


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

$T_j = 25^\circ\text{C}; t_p = 300\text{ }\mu\text{s}$

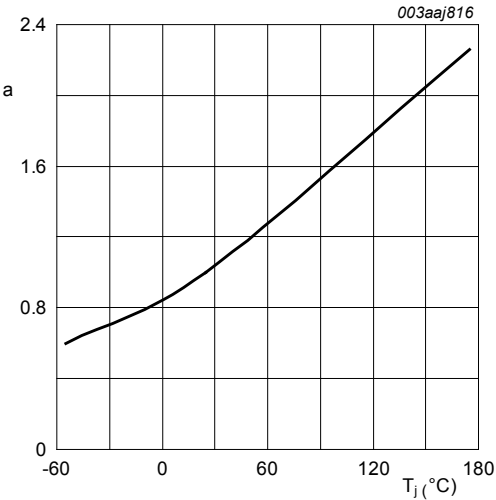


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DS(on)}}{R_{DS(on)}(25^{\circ}\text{C})}$$

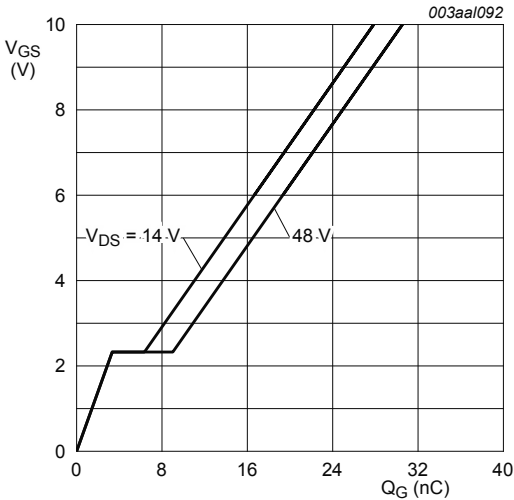


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}\text{C}; I_D = 10\text{ A}$$

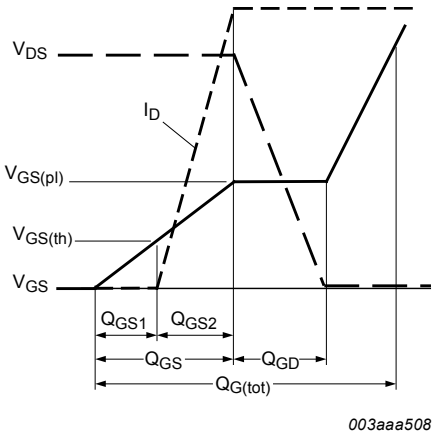


Fig. 13. Gate charge waveform definitions

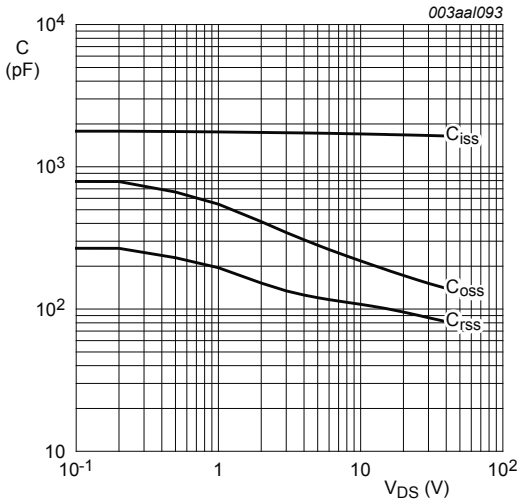


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$$



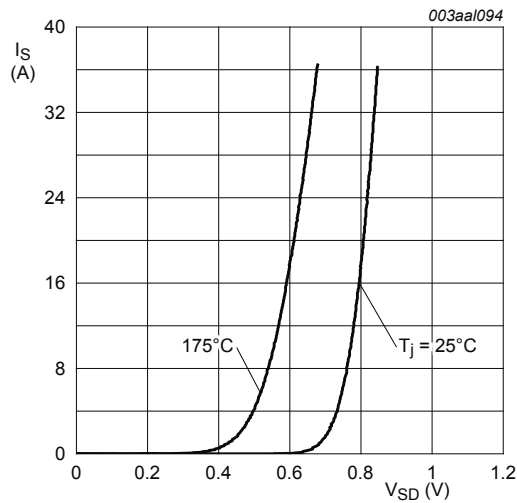


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$V_{GS} = 0V$

11. Package outline

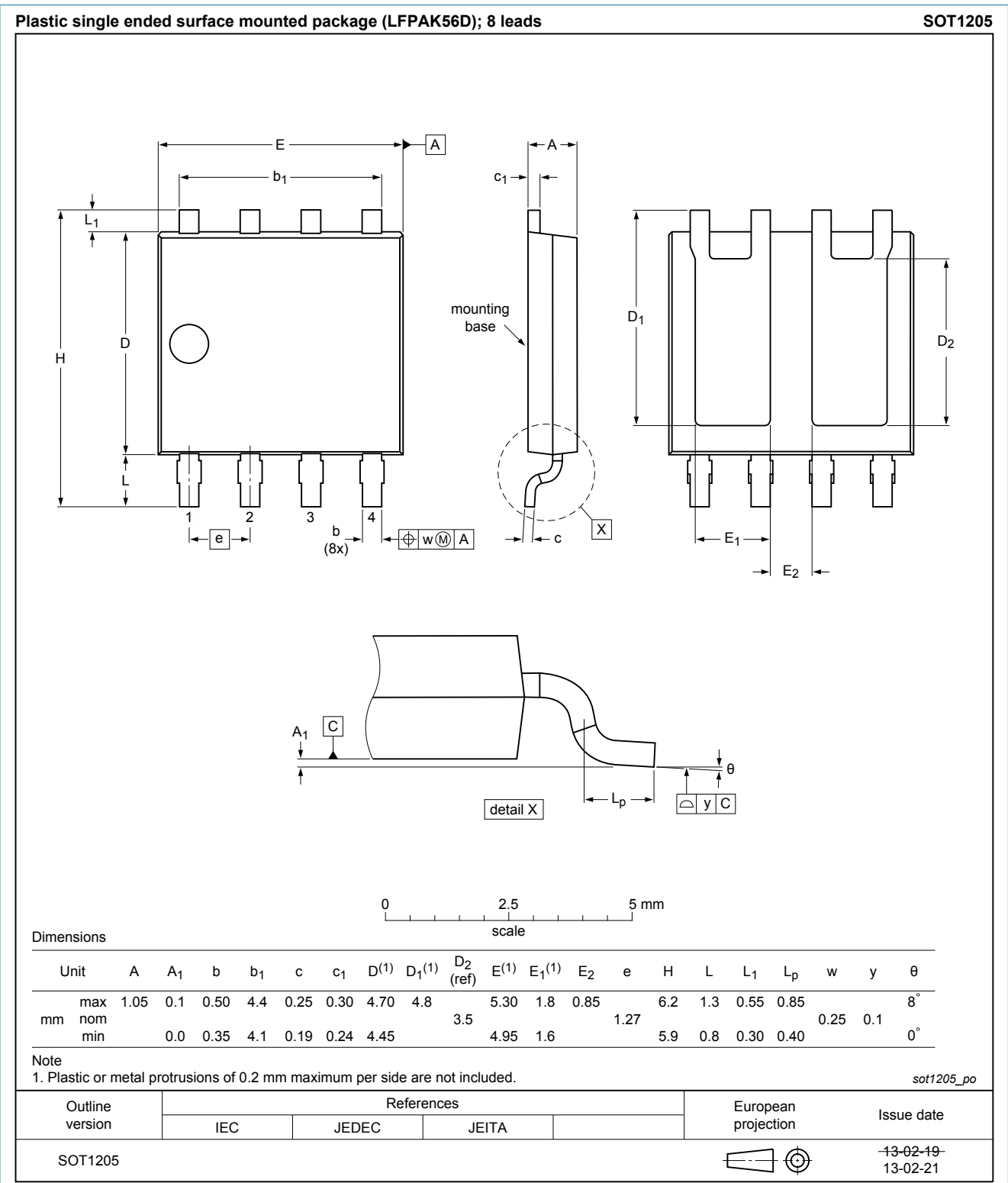


Fig. 17. Package outline LPAK56D (SOT1205)

## 12. Legal information

### 12.1 Data sheet status

| Document status [1][2]         | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

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For more information, please visit: <http://www.nexperia.com>  
For sales office addresses, please send an email to: [salesaddresses@nexperia.com](mailto:salesaddresses@nexperia.com)  
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